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Contents

Authors İΧ Conference Committee xiii ΧVİİ Introduction NIR/SWIR I 10177 02 Performance estimation for SWIR cameras under OH night airglow illumination [10177-1] 10177 03 Development of low-SWaP and low-noise InGaAs detectors [10177-2] 10177 05 Recent advances in InAs/InAs_{1-x}Sb_x/AlAs_{1-x}Sb_x gap-engineered type-II superlattice-based photodetectors (Invited Paper) [10177-4] 10177 06 Al/Sb free InGaAs unipolar barrier infrared detectors [10177-5] 10177 07 Low-noise readout circuit for SWIR focal plane arrays [10177-6] 10177 08 Progress on MCT SWIR modules for passive and active imaging applications [10177-7] 10177 09 Extended spectrum SWIR camera with user-accessible Dewar [10177-8] NIR/SWIR II 10177 0A Numerical modeling of a dark current suppression mechanism in IR detector arrays [10177-9] 10177 OB Functionalization of graphene by size and doping control and its optoelectronic applications [10177-10] 10177 0C Military reconnaissance platform for the spectral range from the visible to the MWIR [10177-11] IR IN AIR AND SPACE 10177 0G Recent progress of push-broom infrared hyper-spectral imager in SITP (Invited Paper) [10177-14] Infrared hyperspectral imaging miniaturized for UAV applications (Invited Paper) [10177-15] 10177 OH 10177 OJ MWIR hyperspectral imaging with the MIDAS instrument (Invited Paper) [10177-17]

10177 OK	CubeSat infrared atmospheric sounder (CIRAS) NASA InVEST technology demonstration (Invited Paper) [10177-18]
10177 OL	Turret indirect vision systems (TIVS) replacing episcopes on armored fighting vehicles [10177-102]
	T2SL: VISTA I
10177 ON	Antimonide type-II superlattice barrier infrared detectors (Invited Paper) [10177-22]
10177 OT	Advances in III-V based dual-band MWIR/LWIR FPAs at HRL (Invited Paper) [10177-28]
10177 OU	Advances in III-V bulk and superlattice-based high operating temperature MWIR detector technology (Invited Paper) [10177-29]
	T2SL: NON-VISTA
10177 11	Photodetector development at Fraunhofer IAF: From LWIR to SWIR operating from cryogenic close to room temperature [10177-36]
10177 12	Growth and characterization of $In_{1-x}Ga_xAs/InAs_{0.65}Sb_{0.35}$ strained layer superlattice infrared detectors [10177-37]
10177 13	T2SL production and development at IRnova: From MWIR to VLWIR detection [10177-38]
10177 14	Development of Type-II superlattice VLWIR detectors in JAXA [10177-40]
10177 15	InAs/GaSb type-II superlattice infrared detectors: three decades of development [10177-99]
	KEYNOTE SESSION
10177 16	The development of the infrared technology for meteorological satellites in Shanghai Institute of Technical Physics (Keynote Paper) [10177-41]
	SUBSTRATES
10177 17	Bulk growth and surface characterization of epitaxy ready cadmium zinc telluride substrates for use in IR imaging applications [10177-42]
10177 18	Large-format multi-wafer production of 5" GaSb-based photodetectors by molecular beam epitaxy [10177-43]

	HGCDTE
10177 19	Response time improvement of LWIR HOT MCT detectors [10177-44]
10177 1A	Ultra-compact high-performance MCT MWIR engine [10177-45]
10177 1B	Simulation of infrared avalanche photodiodes from first principles [10177-46]
10177 1C	Microstructure characterization of lattice defects induced by As ion implantation in HgCdTe epilayers [10177-47]
10177 1D	General review of multispectral cooled IR development at CEA-Leti, France [10177-48]
10177 1E	Latest improvements on long wave p on n HgCdTe technology at Sofradir [10177-49]
10177 1G	Daphnis 10µm pixel pitch product: optimized product and process postponements allowing outstanding on-time delivery [10177-51]
10177 1H	A comparative design study for MWIR HgCdTe detectors [10177-52]
	нот і
10177 11	10µm pitch family of InSb and XBn detectors for MWIR imaging [10177-53]
10177 1J	Fabrication of small pitch, high definition (HD) 1kx2k/5µm MWIR focal-plane-arrays operating at high temperature (HOT) [10177-54]
10177 1K	State-of-the-art MCT photodiodes for cutting-edge sensor applications by AIM [10177-55]
10177 1L	MWIR barrier infrared detectors with greater than 5µm cutoff using bulk InAsSb grown on GaSb substrates [10177-56]
10177 1M	High quantum efficiency mid-wavelength infrared superlattice photodetector [10177-59]
	нот п
10177 10	Heterojunction phototransistor for highly sensitive infrared detection [10177-60]
10177 1P	Evidence of carrier localization in InAsSb/InSb digital alloy nBn detector [10177-61]
10177 1Q	Effects of epitaxial structure and processing on electrical characteristics of InAs-based nBn infrared detectors [10177-62]
	UNCOOLED FPAS AND APPLICATIONS
10177 1R	Novel vacuum packaged 384×288 broadband bolometer FPA with enhanced absorption in the 3-14µm wavelength range [10177-63]

10177 1S	High-performance mushroom plasmonic metamaterial absorbers for infrared polarimetric imaging [10177-64]
10177 1T	Uncooled infrared photodetectors based on one-dimensional nanowires and two-dimensional materials (Invited Paper) [10177-65]
10177 1U	A low-power CMOS readout IC design for bolometer applications [10177-66]
10177 1W	Spectral response of microbolometers for hyperspectral imaging [10177-69]
10177 1X	An 80x80 microbolometer type thermal imaging sensor using the LWIR-band CMOS infrared (CIR) technology [10177-100]
10177 1Y	An advanced presence detection system using the CMOS Infrared (CIR) technology [10177-101]
	ROIC
10177 1Z	A PFM-based MWIR DROIC employing off-pixel fine conversion of photocharge to digital using integrated column ADCs [10177-70]
10177 20	Development of a fully programmable ROIC with 15 μm pixel pitch for MWIR applications [10177-71]
	SMART PROCESSING
10177 25	Small pixel infrared sensor technology (Invited Paper) [10177-78]
	A WORD FROM THE MASTERS
10177 26	Infrared engineering for the advancement of science: A UK perspective (Invited Paper) [10177-79]
10177 27	My life in IRFPA Research and Development (Invited Paper) [10177-80]
	QWIP AND Q-DOTS
10177 29	Effects of doping on photoelectron kinetics and characteristics of quantum dot infrared
10177 29	photodetector [10177-82]
10177 2A	Resonator-QWIPs for 10.6 micron detection [10177-83]
10177 2B	Towards flexible quantum well infrared photodetectors [10177-84]
10177 2C	Novel high-resolution VGA QWIP detector [10177-85]

POSTER SESSION

10177 2D	Minority carrier diffusion lengths and mobilities in low-doped n-InGaAs for focal plane array applications [10177-86]
10177 2E	Effect of insulator layer in graphene plasmonic metamaterials for infrared detection [10177-87]
10177 2G	Remote pedestrians detection at night time in FIR Image using contrast filtering and locally projected region based CNN [10177-89]
10177 2H	A study on inductively coupled plasma etch rate of HgCdTe at cryogenic temperature [10177-90]
10177 2I	Forward looking infrared imagery for landmine detection [10177-91]
10177 2J	Design and fabrication of metal-insulator-metal diode for high frequency applications [10177-92]
10177 2K	Array size and area impact on nanorectenna performance properties [10177-94]
10177 2L	Standardizing large format 5" GaSb and InSb substrate production [10177-95]
10177 2M	Short wavelength infrared photodetector and light emitting diode based on InGaAsSb [10177-96]